

#### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-20V	0.9Ω @ V <sub>GS</sub> = -4.5V	-0.53A
	1.4Ω @ V <sub>GS</sub> = -2.5V	-0.44A

### **Description**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

### **Applications**

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

#### **Features**

- Dual P-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage V<sub>GS(TH)</sub> < 1V</li>
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

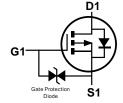
#### **Mechanical Data**

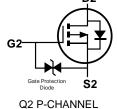
- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (Approximate)

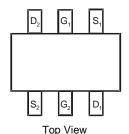












Pin Out

Top View

Bottom View

**SOT563** 

Q1 P-CHANNEL MOSFET

MOSFET

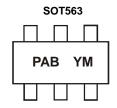
**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP2004VK-7	SOT563	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



PAB = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

Year	2007			2015	2016	20	17	2018	2019	20	20	2021
Code	J			С	D	[	Ξ	F	G	H	1	I
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		$V_{DSS}$	-20	V	
Gate-Source Voltage		$V_{GSS}$	±8	V	
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-0.53 -0.44	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = -2.5V	I <sub>D</sub>	-0.44 -0.35	А		
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-1.8	А	

### **Thermal Characteristics**

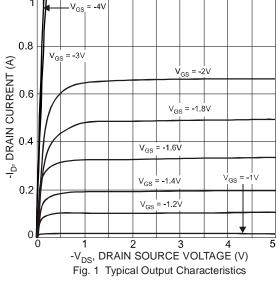
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	400	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	312	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-65 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			0.7	0.9		$V_{GS} = -4.5V$ , $I_D = -430mA$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	1.1	1.4	Ω	$V_{GS} = -2.5V, I_D = -300mA$
			1.7	2.0		$V_{GS} = -1.8V, I_D = -150mA$
Forward Transfer Admittance	Y <sub>fs</sub>	200	_	_	mS	$V_{DS} = -10V, I_{D} = -0.2A$
Diode Forward Voltage (Note 5)	$V_{SD}$	-0.5	_	-1.2	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	_	_	175	pF	10/1/
Output Capacitance	Coss	_	_	30	pF	$V_{DS} = -16V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	20	pF	71 = 1.0IVII 12

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.





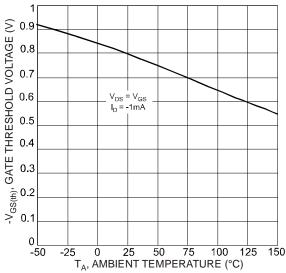
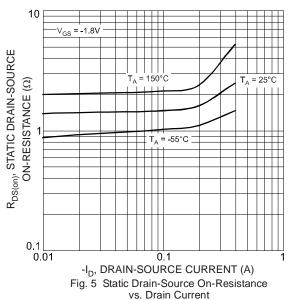
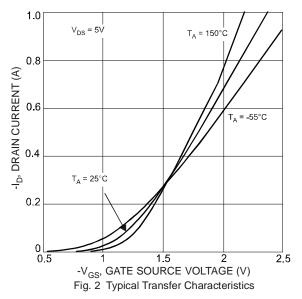


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature





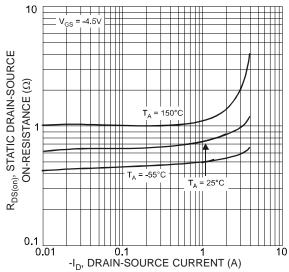


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

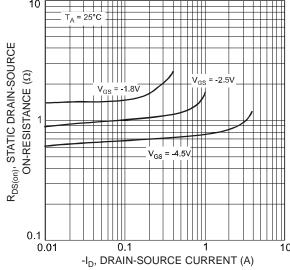


Fig. 6 Static Drain-Source On-Resistance vs.
Drain-Source Current



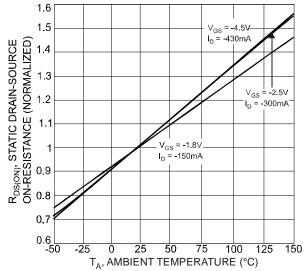


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

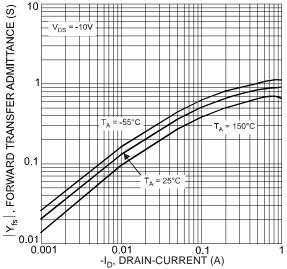


Fig. 9 Forward Transfer Admittance vs. Drain-Current

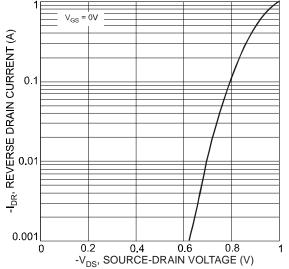
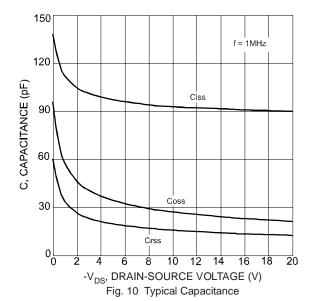


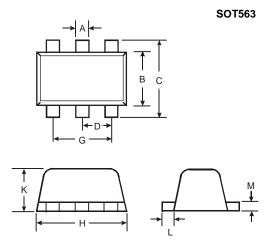
Fig. 8 Reverse Drain Current vs. Source-Drain Voltage





## **Package Outline Dimensions**

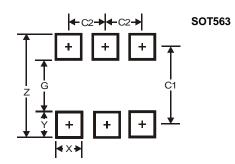
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
С	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	0.55	0.60	0.60				
L	0.10	0.30	0.20				
M	0.10	0.18	0.11				
All Dimensions in mm							

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



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